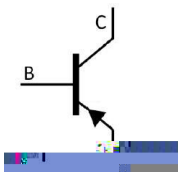
WR0<50P ḾḾÞ SQS ÆḾч s ll ㄱ Silicon PNP transistor in a TO-92LM Plastic Package.

лъ 5VG99:+D,Ӣ´
Complementary pair with 2SD667(A).

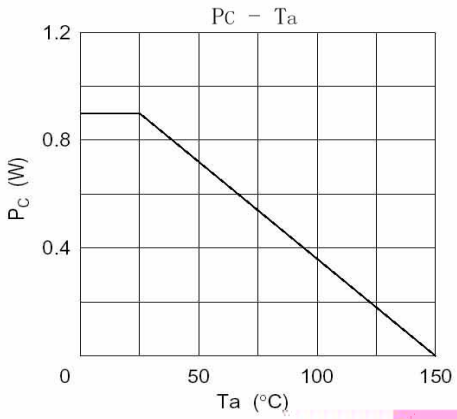
ᵮ Ӈ ļ ı ' ѽ ᶻ
Low frequency power amplifier.

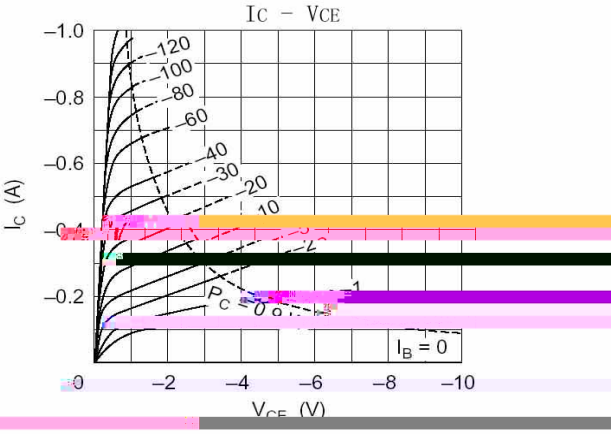


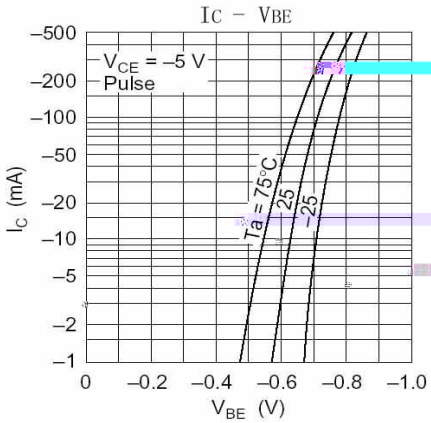


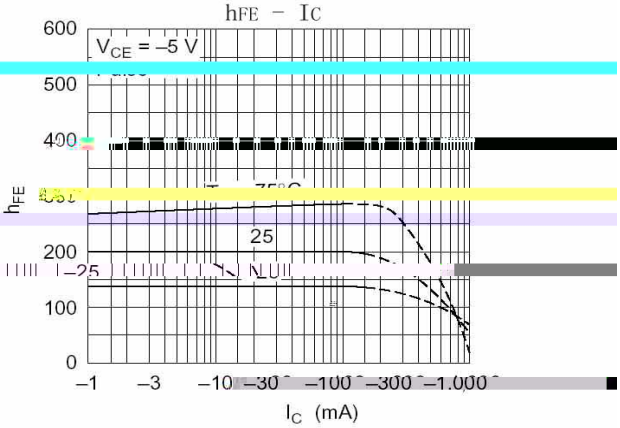
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

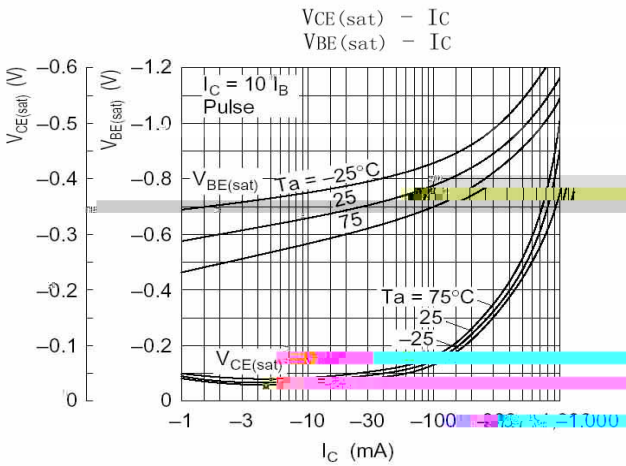
v Ѽ Parameter	ϒ N Symbol		Ѽ Ө Rating	D Ң Unit
Collector to Base Voltage	V_{CBO}		-120	V
Collector to Emitter Voltage	V_{CEO}	2SB647	-80	V
		2SB647A	-100	
Emitter to Base Voltage	V_{EBO}		-5.0	V
Collector Current (DC)	I_C		-1.0	A
Collector Current(Pulse)	I_{CP}		-2.0	A
Collector Power Dissipation	P_C		900	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T			

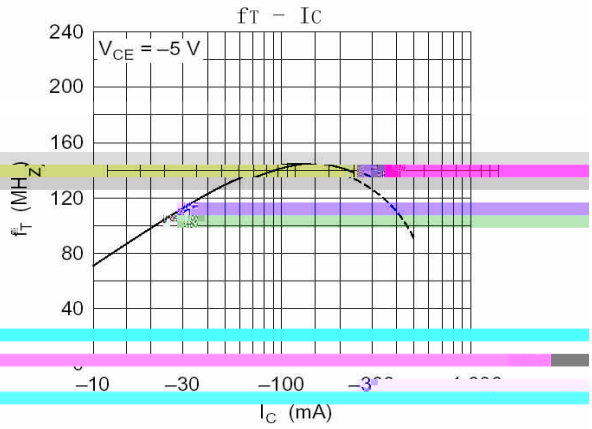

PC – Ta
PC (W)
1.2
0.8
0.4
0
50
100
150
Ta (°C)


IC – VCE
IC (A)
–1.0
–0.8
–0.6
–0.2
120
100
80
60
40
30
20
10
IB = 0
–2
–4
–6
–8
–10


IC – VBE
VCE = –5 V
Pulse
IC (mA)
–500
–200
–100
–50
–20
–10
–5
–2
–1
Ta = 75°C
25
–25
0
–0.2
–0.4
–0.6
–0.8
–1.0
VBE (V)

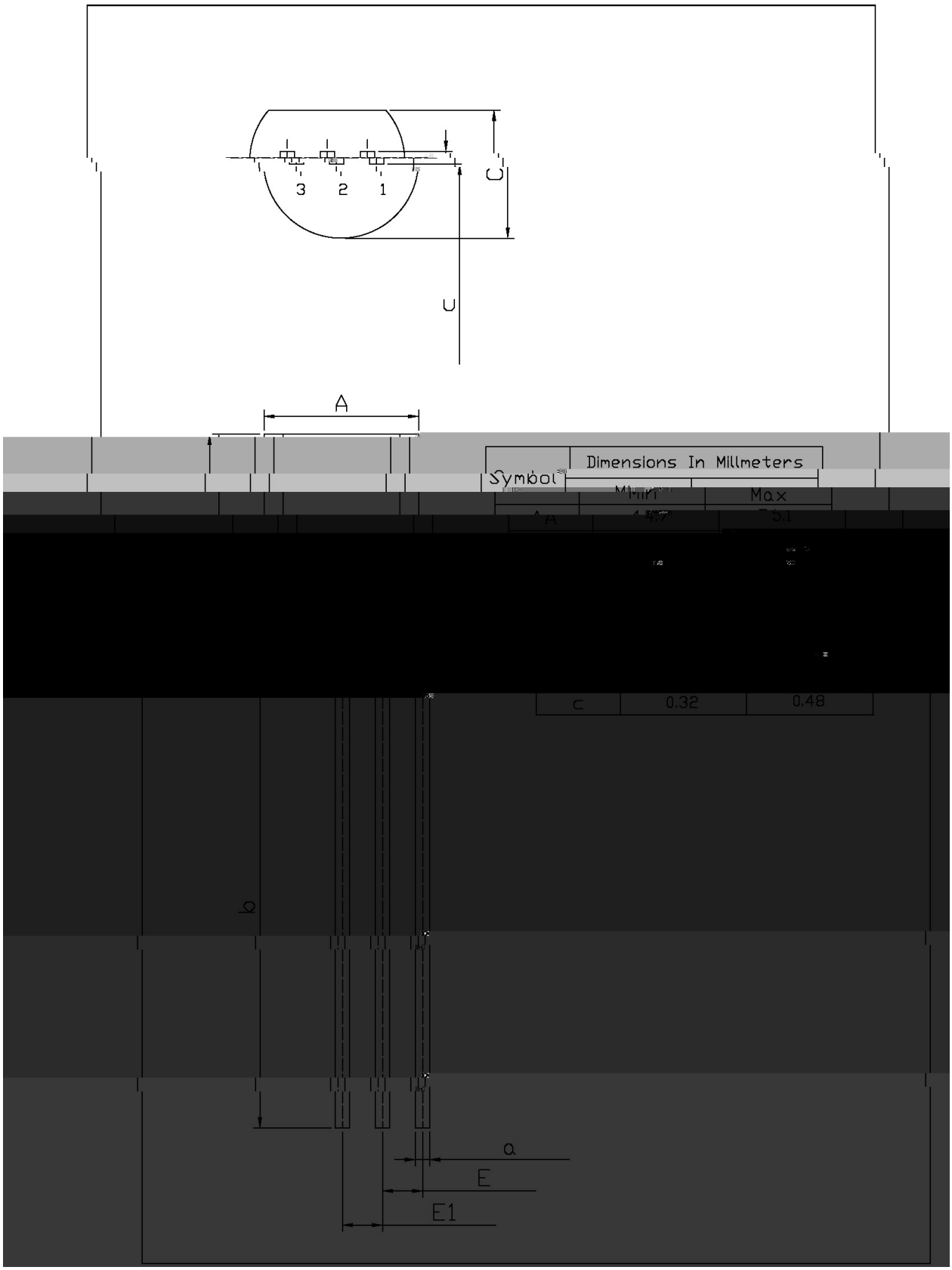

hFE – IC
VCE = –5 V
hFE
600
500
400
200
100
0
25
–25
–1
–3
–10
–30
–100
–300
–1,000
IC (mA)


VCE(sat) – IC
VBE(sat) – IC
IC = 10 IB
Pulse
VCE(sat) (V)
VBE(sat) (V)
–0.6
–0.5
–0.4
–0.3
–0.2
–0.1
0
–1.2
–1.0
–0.8
–0.6
–0.4
–0.2
VBE(sat)
Ta = –25°C
25
75
Ta = 75°C
25
–25
VCE(sat)
–1
–3
–10
–30
–100
–1,000
IC (mA)


fT – IC
VCE = –5 V
fT (MHz)
240
200
160
120
80
40
–10
–30
–100
IC (mA)

TO-92LM

Unit: mm

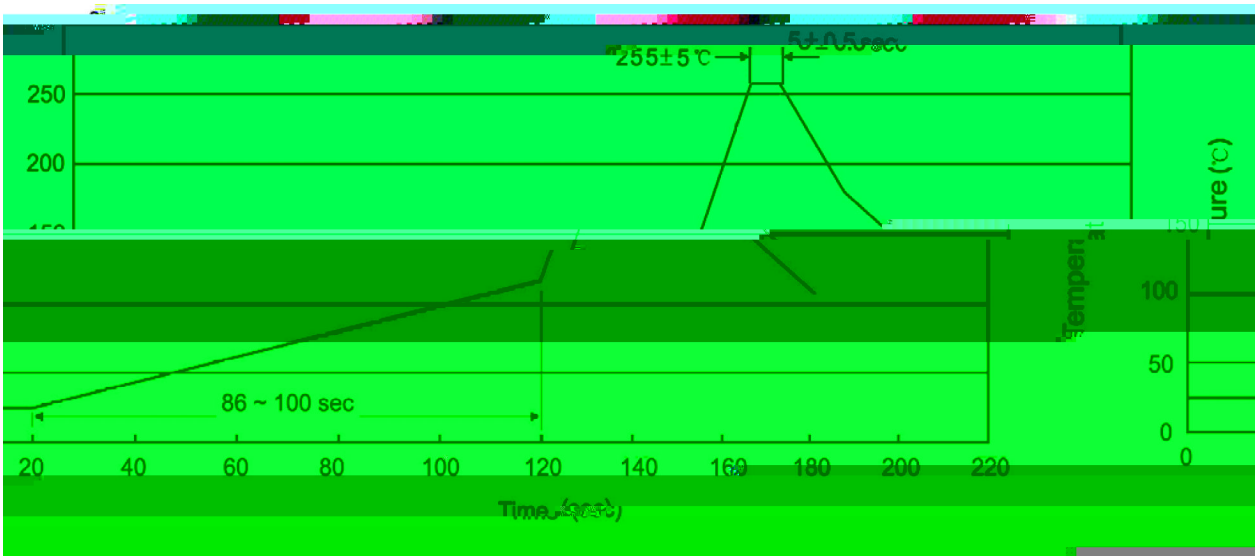




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EU=	ᵻᵡ ϛ ᴎ Γϧ
E97 : D χ	ᵻᵡ ʒ ᴺ Γϧ
F=	ᵻᵡ k ᵻᴴ ᶜ ⁶ Γϧ
---- χ	ᵻᵡ ᵻ ᶠ ᵑ̋ ᴺ Γϧ ᵻ ᵩ ᵻ ᶠ ᵑ̋ ᴺ Ψ ᖘ

Note:

BR:	Company Code.
B647A:	Product Type.
C:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

Note:

1.Preheating:25~150 ł